



FOURTH EDITION

CMOS VLSI DESIGN

A CIRCUITS
AND
SYSTEMS
PERSPECTIVE

NEIL H. E. WESTE

DAVID MONEY HARRIS

CMOS VLSI Design

A Circuits and Systems Perspective

Fourth Edition

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A Circuits and Systems Perspective

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*To Avril, Melissa, Tamara, Nicky, Jocelyn,
Makayla, Emily, Danika, Dan and Simon*
N. W.

To Jennifer, Samuel, and Abraham
D. M. H.

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